DATA SHEET

BST100
P-channel enhancement mode vertical D-MOS transistor

Product specification
File under Discrete Semiconductors, SC13b

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Philips Semiconductors

PHILIPS

P-channel enhancement mode vertical D-MOS transistor

BST100

DESCRIPTION

P-channel vertical D-MOS transistor TO-92 variant envelope and intended for use in relay, high-speed and line-transformer drivers.

FEATURES

- Very low $R_{DS(on)}$
- Direct interface to C-MOS
- High-speed switching
- No second breakdown

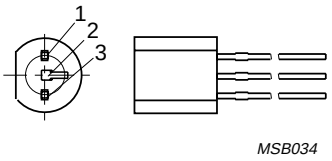
QUICK REFERENCE DATA

Drain-source voltage	$-V_{DS}$	max.	60	V
Gate-source voltage (open drain)	$\pm V_{GSO}$	max.	20	V
Drain current (DC)	$-I_D$	max.	0.3	A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1	W
Drain-source ON-resistance				
$-I_D$ = 200 mA; $-V_{GS}$ = 10 V	$R_{DS(on)}$	typ. max.	4,5 6	Ω Ω
Transfer admittance				
$-I_D$ = 200 mA; $-V_{DS}$ = 15 V	$\lvert Y_{fs} \rvert$	typ.	200	mS

PINNING - TO-92 VARIANT

1 = source
2 = gate
3 = drain

PIN CONFIGURATION



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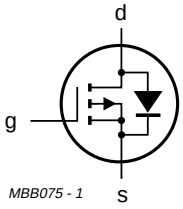

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Note: various pinout configurations available.

Fig.1 Simplified outline and symbol.

P-channel enhancement mode vertical D-MOS transistor

BST100

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	$-V_{DS}$	max.	60	V
Gate-source voltage (open drain)	$\pm V_{GSO}$	max.	20	V
Drain current (DC)	$-I_D$	max.	0.3	A
Drain current (peak)	$-I_{DM}$	max.	0.8	A
Total power dissipation up to T_{amb} = 25 °C (note 1)	P_{tot}	max.	1	W
Storage temperature range	T_{stg}		−65 to + 150	°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to ambient (note 1)	$R_{th\ j\text{-}a}$	=	125	K/W

Note

1. Transistor mounted on printed-circuit board, max. lead length 4 mm, mounting pad for drain lead min. 10 mm x 10 mm.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Drain-source breakdown voltage				
$-I_D$ = 10 μA; V_{GS} = 0	$-V_{(BR)DSS}$	min.	60	V
Drain-source leakage current				
$-V_{DS}$ = 48 V; V_{GS} = 0	$-I_{DSS}$	max.	1	μA
Gate-source leakage current				
$-V_{GS}$ = 20 V; V_{DS} = 0	$-I_{GSS}$	max.	100	nA
Gate threshold voltage				
$-I_D$ = 1 mA; V_{DS} = V_{GS}	$-V_{GS(th)}$	min.	1.5	V
		max.	3.5	V
Drain-source ON-resistance				
$-I_D$ = 200 mA; $-V_{GS}$ = 10 V	$R_{DS(on)}$	typ.	4.5	Ω
		max.	6	Ω
Transfer admittance				
$-I_D$ = 200 mA; $-V_{DS}$ = 15 V	$\lvert Y_{fs} \rvert$	typ.	200	mS
Input capacitance at f = 1 MHz				
$-V_{DS}$ = 10 V; V_{GS} = 0	C_{iss}	typ.	55	pF
		max.	70	pF
Output capacitance at f = 1 MHz				
$-V_{DS}$ = 10 V; V_{GS} = 0	C_{oss}	typ.	30	pF
		max.	45	pF
Feedback capacitance at f = 1 MHz				
$-V_{DS}$ = 10 V; V_{GS} = 0	C_{rss}	typ.	8	pF
		max.	12	pF
Switching times (see Figs 2 and 3)				
$-I_D$ = 200 mA; $-V_{DD}$ = 50 V; $-V_{GS}$ = 0 to 10 V	t_{on}	typ.	4	ns
	t_{off}	typ.	20	ns

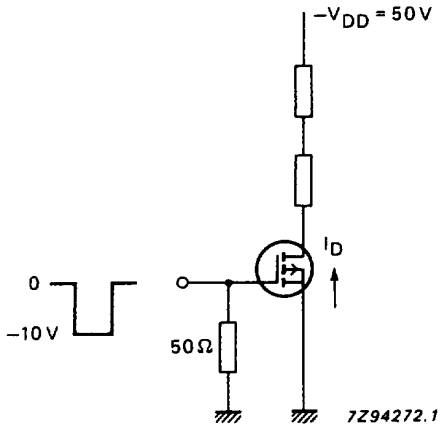


Fig.2 Switching times test circuit.

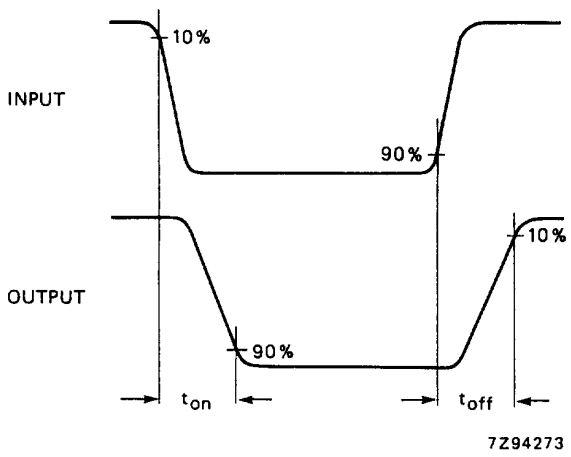


Fig.3 Input and output waveforms.

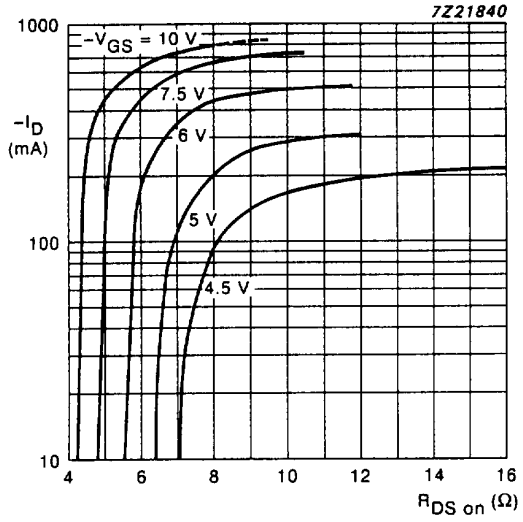


Fig.4 Drain current vs ON-resistance.
T_j = 25 °C; typical values.

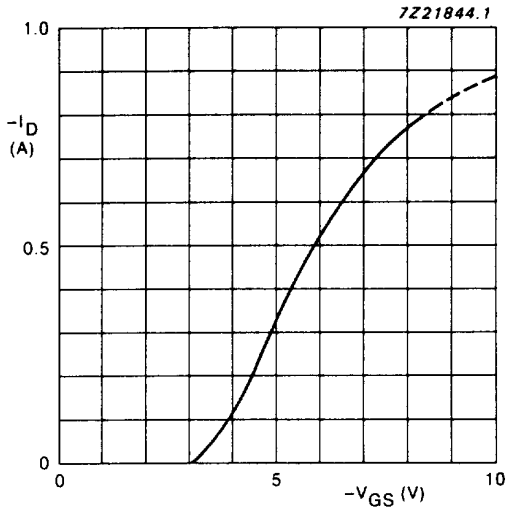


Fig.5 Transfer characteristics.
T_j = 25 °C; $-V_{DS}$ = 10 V; typical values.

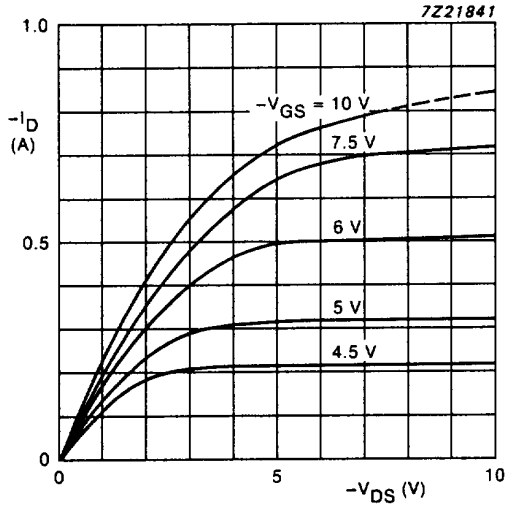
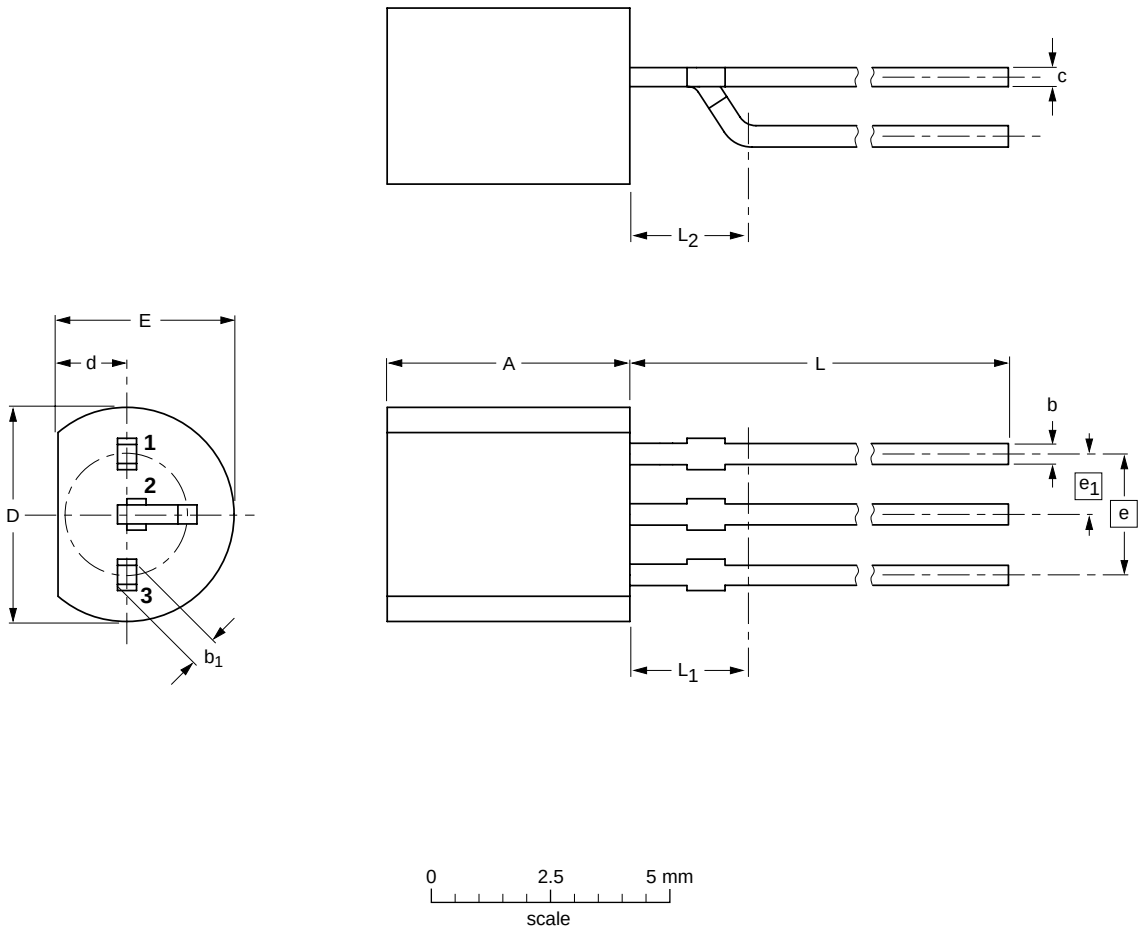


Fig.6 Output characteristics. T_j = 25 °C; typical values.

PACKAGE OUTLINES

Plastic single-ended leaded (through hole) package; 3 leads (on-circle) **SOT54 variant**



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b_1	c	D	d	E	e	e_1	L	L_1 (1) max	L_2 max
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5	2.5

Notes

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT54 variant		TO-92	SC-43			97-04-14

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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